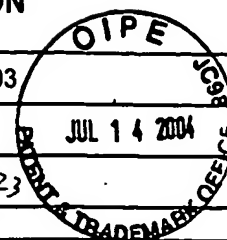


## INFORMATION DISCLOSURE CITATION

Atty. Docket No.	2887.0261	Appln. No.	10/730,903
Applicant	Saito		
Filing Date	December 10, 2003	Group:	28112823



U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
QWB		6,054,355	4/25/00	Inumiya et al.	438	296	X

FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
QWB		2000-294557	10/20/00	Japan	X	X	Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
QWB	Saito et al., "Plasma-Damage-Free Gate Process Using Chemical Mechanical Polishing for 0.1 $\mu$ m MOSFETs," Jpn. J. Appl. Phys. (April 1999), 38:2227-31

Examiner	William M. Brenner	Date Considered	AUG 5
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## INFORMATION DISCLOSURE CITATION

Patent No. 02887.0261	Application No. 10/730,903
Applicant Tomohiro SAITO	
Filing Date December 10, 2003	Group: 28TT 2823

## U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

## FOREIGN PATENT DOCUMENTS

	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
W/P	04-123439	04/23/1992	Japan	X	X	Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)


Examiner William M. Brunster	Date Considered 6 AUG 05
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